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Team Nexperia



60 V, 10 A PNP high power bipolar transistor 27 May 2015

Product data sheet

### 1. General description

PNP high power bipolar transistor in a SOT669 (LFPAK56) Surface-Mounted Device (SMD) power plastic package.

NPN complement: PHPT60610NY

### 2. Features and benefits

- High thermal power dissipation capability
- High temperature applications up to 175 °C
- Reduced Printed Circuit Board (PCB) requirements comparing to transistors in DPAK
- High energy efficiency due to less heat generation
- AEC-Q101 qualified.

### 3. Applications

- Power management
- Load switch
- Linear mode voltage regulator
- Backlighting applications
- Motor drive
- Relay replacement

### 4. Quick reference data

Table 1.   Quick reference data							
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>CEO</sub>	collector-emitter voltage	open base		-	-	-60	V
I <sub>C</sub>	collector current			-	-	-10	А
I <sub>CM</sub>	peak collector current	$t_p \le 1 \text{ ms}; \text{ pulsed}$		-	-	-20	А
R <sub>CEsat</sub>	collector-emitter saturation resistance	$\begin{split} I_C &= -10 \text{ A};  I_B = -1 \text{ A};  t_p \leq 300  \mu\text{s}; \\ \delta &\leq 0.02;  T_{amb} = 25 ^\circ\text{C}; \text{ pulsed} \end{split}$		-	29	47	mΩ





60 V, 10 A PNP high power bipolar transistor

# 5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	E	emitter	mb	С
2	Е	emitter		в
3	E emitter	q	۲۳ - ۲۳ - ۲۳ - ۲۳ - ۲۳ - ۲۳ - ۲۳ - ۲۳ -	
4	В	base	មុប្បូប្	sym132
mb	С	collector	1 2 3 4 LFPAK56; Power- SO8 (SOT669)	

# 6. Ordering information

Table 3.       Ordering information					
Type number	Package				
	Name	Description	Version		
PHPT60610PY	LFPAK56; Power-SO8	Plastic single-ended surface-mounted package (LFPAK56; Power-SO8); 4 leads	SOT669		

# 7. Marking

Table 4. Marking codes	
Type number	Marking code
PHPT60610PY	0610PAB

60 V, 10 A PNP high power bipolar transistor

### 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

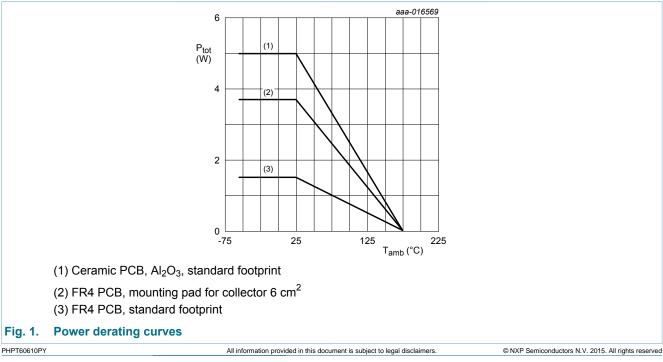
Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>CBO</sub>	collector-base voltage	open emitter		-	-60	V
V <sub>CEO</sub>	collector-emitter voltage	open base		-	-60	V
V <sub>EBO</sub>	emitter-base voltage	open collector		-	-8	V
I <sub>C</sub>	collector current			-	-10	А
I <sub>CM</sub>	peak collector current	$t_p \le 1 ms$ ; pulsed		-	-20	А
I <sub>B</sub>	base current			-	-1.5	А
I <sub>BM</sub>	peak base current	$t_p \le 1 ms$ ; pulsed		-	-2	А
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	1.5	W
			[2]	-	3.7	W
			[3]	-	5	W
			[4]	-	25	W
Tj	junction temperature			-	175	°C
T <sub>amb</sub>	ambient temperature			-55	175	°C
T <sub>stg</sub>	storage temperature			-65	175	°C

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated mounting pad for collector 6 cm<sup>2</sup>.

[3] Device mounted on a ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint.

[4] Power dissipation from junction to mounting base.



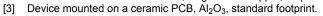
60 V, 10 A PNP high power bipolar transistor

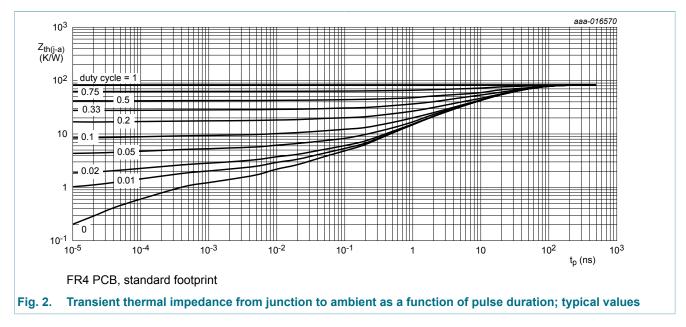
### 9. Thermal characteristics

Table 6. The	Table 6. Thermal characteristics						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
1	thermal resistance from junction to ambient	in free air	[1]	-	-	100	K/W
		-	[2]	-	-	41	K/W
			[3]	-	-	30	K/W
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base			-	-	6	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated mounting pad for collector 6 cm<sup>2</sup>.

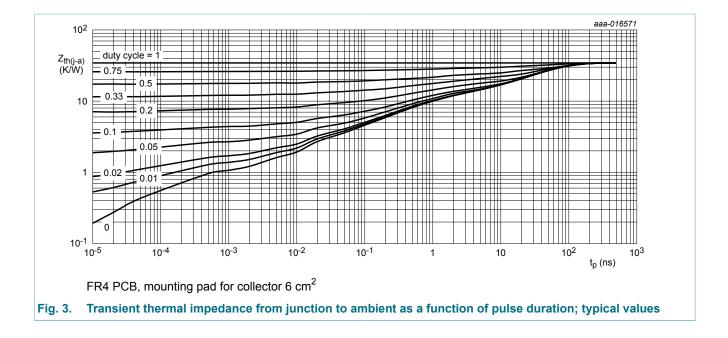




#### **NXP Semiconductors**

# **PHPT60610PY**

#### 60 V, 10 A PNP high power bipolar transistor



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### **10. Characteristics**

Symbol	Parameter	Conditions	M	in T	ур	Max	Unit
I <sub>CBO</sub>	collector-base cut-off	$V_{CB}$ = -48 V; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-		-100	nA
	current	$V_{CB}$ = -48 V; I <sub>E</sub> = 0 A; T <sub>j</sub> = 150 °C	-	-		-50	μA
I <sub>CES</sub>	collector-emitter cut-off current	$V_{CE}$ = -48 V; $V_{BE}$ = 0 V; $T_{amb}$ = 25 °C	-	-		-100	nA
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB}$ = -8 V; $I_{C}$ = 0 A; $T_{amb}$ = 25 °C	-	-		-100	nA
h <sub>FE</sub>	DC current gain	$V_{CE}$ = -2 V; I <sub>C</sub> = -500 mA; T <sub>amb</sub> = 25 °C	1:	20 2	215	-	
		$\label{eq:VCE} \begin{array}{l} V_{CE} = \text{-2 V; } I_{C} = \text{-1 A; } t_{p} \leq 300 \ \mu s; \\ \delta \leq 0.02; \ T_{amb} = 25 \ ^{\circ}C; \ pulsed \end{array}$	1:	20 2	205	-	
		$\begin{split} V_{CE} &= -2 \text{ V; } I_C = -5 \text{ A; } t_p \leq 300  \mu\text{s;} \\ \delta \leq 0.02;  T_{amb} = 25 ^\circ\text{C; } \text{pulsed} \end{split}$	70	) 1	30	-	
		$V_{CE} = -2 \text{ V; } I_C = -10 \text{ A; pulsed;}$ $t_p \le 300  \mu\text{s; } \delta \le 0.02\text{; } T_{amb} = 25 ^\circ\text{C}$	30	) 5	55	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_{C} = -1 \text{ A}; I_{B} = -50 \text{ mA}; t_{p} \le 300 \mu\text{s};$ $\delta \le 0.02; \text{ T}_{amb} = 25 ^{\circ}\text{C}$	-	-	50	-80	mV
		$I_{C} = -5 \text{ A}; I_{B} = -500 \text{ mA}; t_{p} \le 300  \mu\text{s};$ $\delta \le 0.02; \text{ T}_{amb} = 25 ^{\circ}\text{C}; \text{ pulsed}$	-	-	130	-220	mV
		$\begin{split} & \textbf{I}_{C} = -10 \text{ A};  \textbf{I}_{B} = -1 \text{ A}; \text{ pulsed}; \\ & \textbf{t}_{p} \leq 300  \mu\text{s};  \delta \leq 0.02;  \textbf{T}_{amb} = 25 ^{\circ}\text{C} \end{split}$	-	-	290	-470	mV
R <sub>CEsat</sub>	collector-emitter saturation resistance	$I_{C}$ = -10 A; $I_{B}$ = -1 A; $t_{p}$ ≤ 300 µs; δ ≤ 0.02; $T_{amb}$ = 25 °C; pulsed	-	2	29	47	mΩ
V <sub>BEsat</sub>	base-emitter saturation voltage	$I_{C}$ = -1 A; $I_{B}$ = -50 mA; pulsed; $t_{p} \le 300 \ \mu$ s; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	-		-0.95	V
		$I_{C}$ = -5 A; $I_{B}$ = -500 mA; pulsed; $t_{p} \le 300 \ \mu$ s; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	-		-1.1	V
		$I_C$ = -10 A; $I_B$ = -1 A; pulsed; t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	-		-1.3	V
V <sub>BEon</sub>	base-emitter turn-on voltage	$V_{CE}$ = -2 V; I <sub>C</sub> = -500 mA; T <sub>amb</sub> = 25 °C	-	-		-0.9	V
t <sub>d</sub>	delay time	V <sub>CC</sub> = -12.5 V; I <sub>C</sub> = -5 A;	-	2	25	-	ns
t <sub>r</sub>	rise time	I <sub>Bon</sub> = -250 mA; I <sub>Boff</sub> = 250 mA; T <sub>amb</sub> = 25 °C	-	1	05	-	ns
t <sub>on</sub>	turn-on time	amb - 20 0	-	1	30	-	ns
s	storage time		-	1	65	-	ns
f	fall time		-	5	55	-	ns
t <sub>off</sub>	turn-off time		-	2	220	-	ns

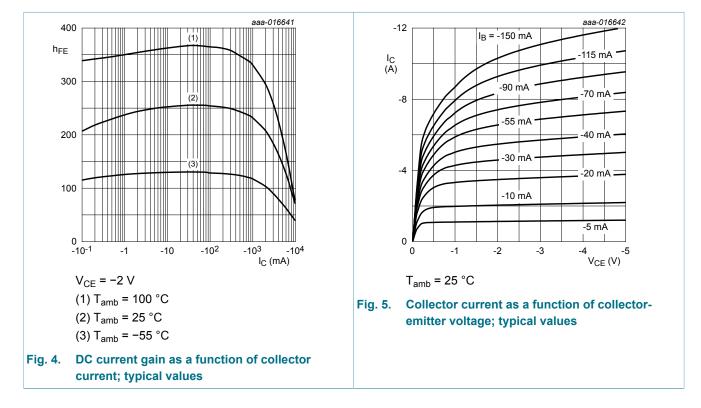
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#### **NXP Semiconductors**

#### 60 V, 10 A PNP high power bipolar transistor

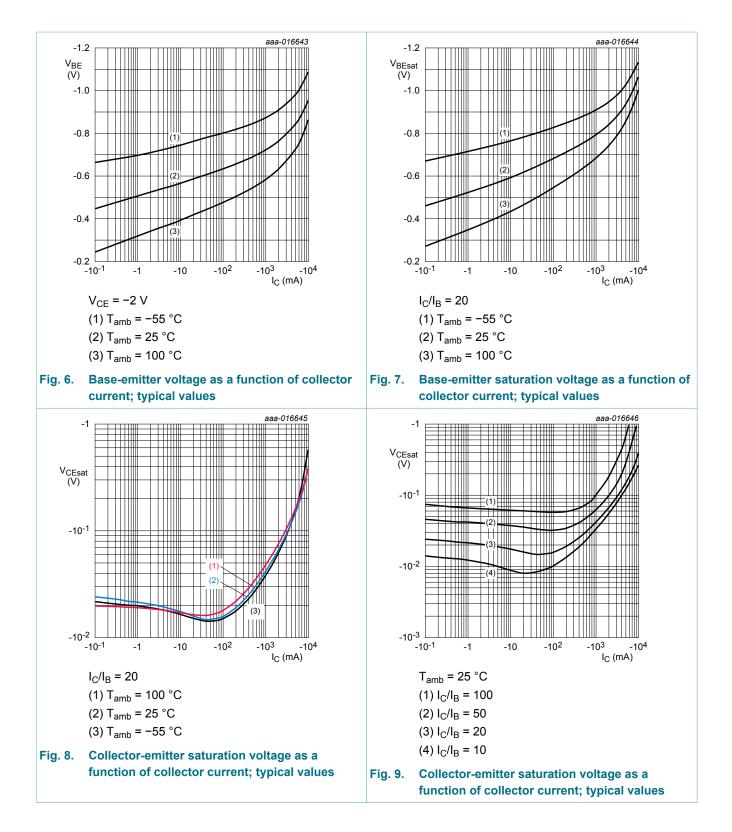
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
f <sub>T</sub>	transition frequency	V <sub>CE</sub> = -10 V; I <sub>C</sub> = -500 mA; f = 100 MHz; T <sub>amb</sub> = 25 °C	-	85	-	MHz
C <sub>c</sub>	collector capacitance	V <sub>CB</sub> = -10 V; I <sub>E</sub> = 0 A; i <sub>e</sub> = 0 A; f = 1 MHz; T <sub>amb</sub> = 25 °C	-	135	-	pF



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#### 60 V, 10 A PNP high power bipolar transistor

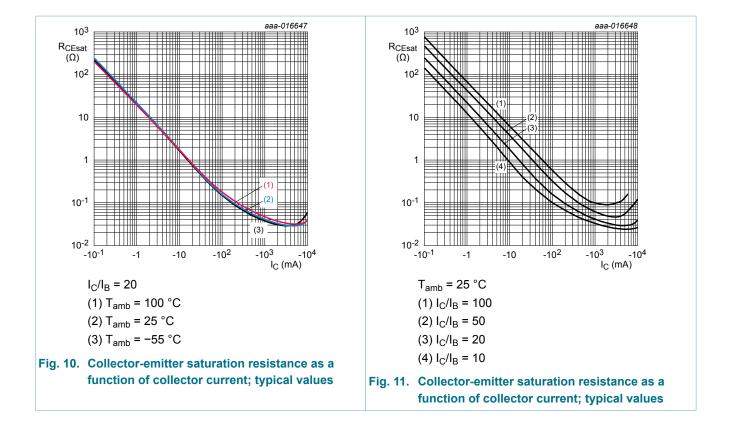


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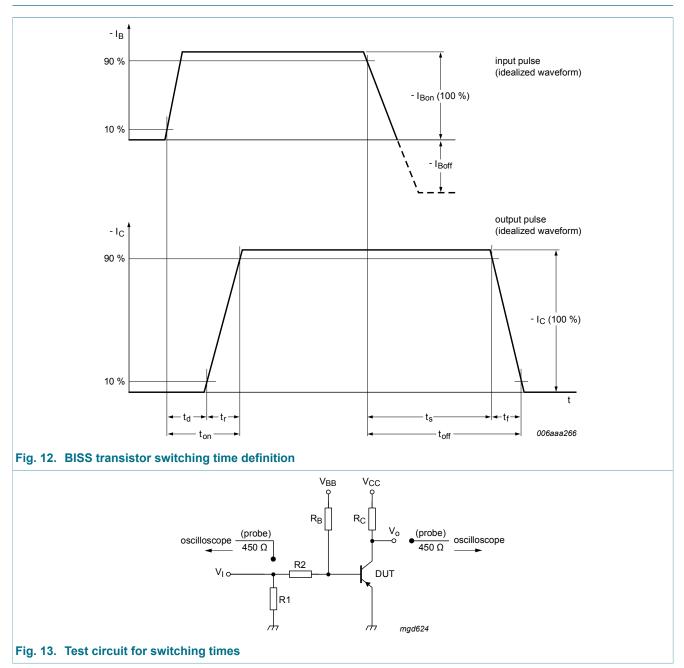
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#### 60 V, 10 A PNP high power bipolar transistor



### 11. Test information

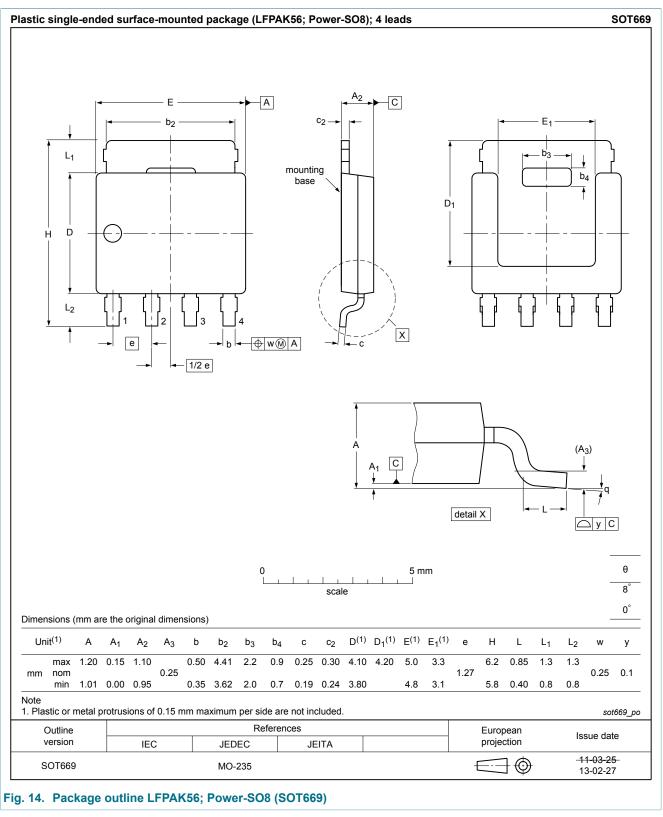


This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

PHPT60610PY

#### 60 V, 10 A PNP high power bipolar transistor

### 12. Package outline



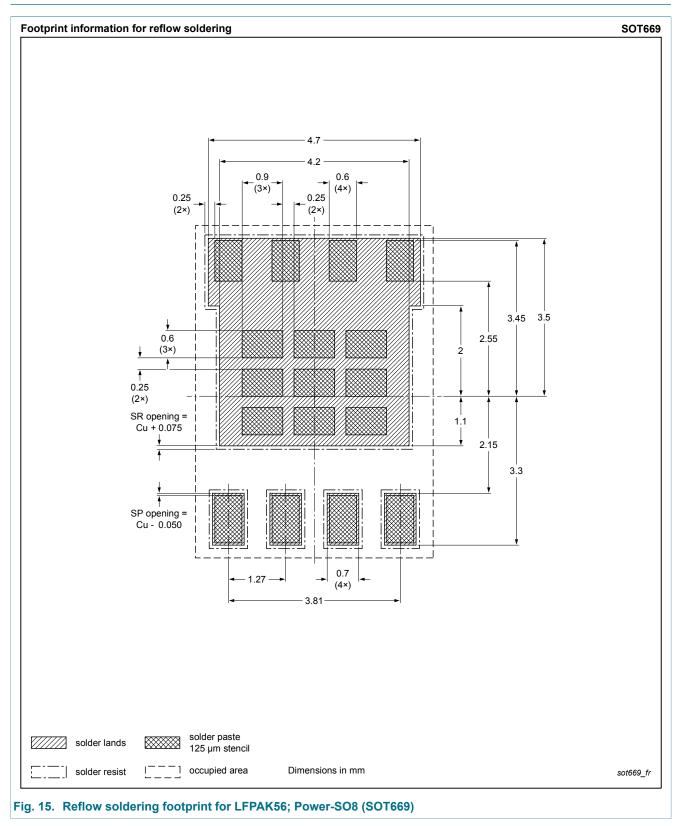
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Product data sheet

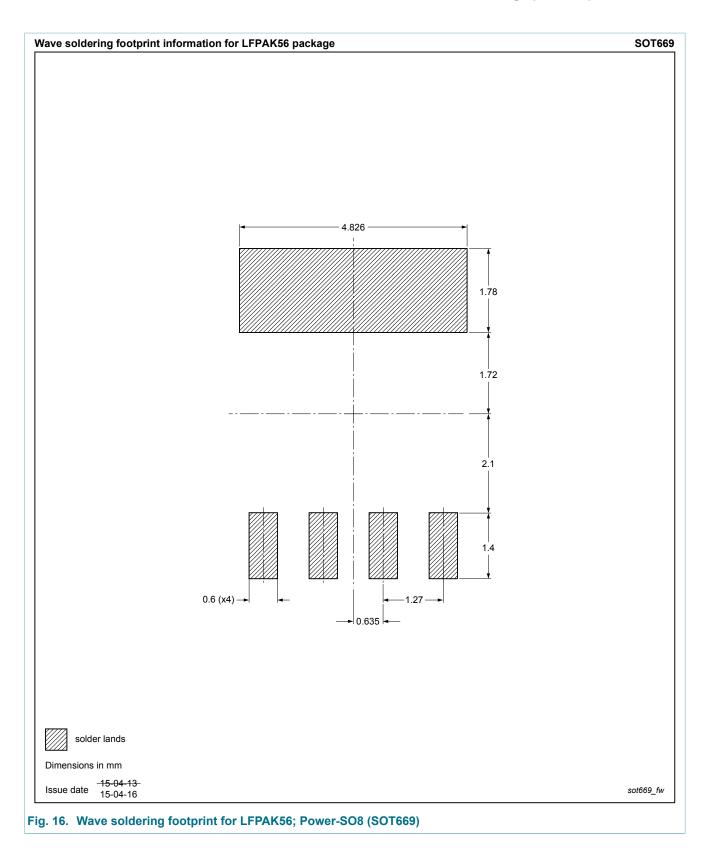
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### 13. Soldering



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#### 60 V, 10 A PNP high power bipolar transistor



#### 60 V, 10 A PNP high power bipolar transistor

# 14. Revision history

Table 8. Revision his	story			
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PHPT60610PY v.1	20150527	Product data sheet	-	-

#### 60 V, 10 A PNP high power bipolar transistor

### 15. Legal information

#### 15.1 Data sheet status

Document status [1][2]	Product status [ <u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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